This technology is currently not available for licensing

Tech ID: 22788

ADDITIONAL TECHNOLOGIES BY THESE INVENTORS

- Vertical Cavity Surface-Emitting Lasers with Continuous Wave Operation
- Eliminating Misfit Dislocations with In-Situ Compliant Substrate Formation
- Enhanced Light Extraction LED with a Tunnel Junction Contact Wafer Bonded to a Conductive Oxide
- Methods to Produce and Recycle Substates for III-Nitride Materials with Electrochemical Etching
- III-Nitride Tunnel Junction with Modified Interface
- Improved Reliability & Enhanced Performance of III-Nitride Tunnel Junction Optoelectronic Devices
- (In,Ga,Al)N Optoelectronic Devices with Thicker Active Layers for Improved Performance
- Thermally Stable, Laser-Driven White Lighting Device
- III-Nitride Tunnel Junction LED with High Wall Plug Efficiency
- A Method To Lift-Off Nitride Materials With Electrochemical Etch
- Activation of P-Type Layers of Tunnel Junctions in Micro-LEDs
- High-Intensity Solid State White Laser Diode
- Nitride Based Ultraviolet LED with an Ultraviolet Transparent Contact
- Epitaxial Light Control Features in Light Emitting Diodes
- High-Efficiency Vertical Cavity Surface Emitting Laser Fabrication
- A Wafer-Scale, Low Defect Density Strain Relaxed Template for III-Nitride-Based High Efficiency and High-Power Devices

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